

CMLDM7003
CMLDM7003G*
CMLDM7003J

**SURFACE MOUNT SILICON
DUAL N-CHANNEL
ENHANCEMENT-MODE
MOSFETS**



SOT-563 CASE

* Device is **Halogen Free** by design



www.centrasemi.com

DESCRIPTION:

These CENTRAL SEMICONDUCTOR devices are dual N-Channel enhancement-mode MOSFETs, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. The CMLDM7003 utilizes the USA pinout configuration, while the CMLDM7003J utilizes the Japanese pinout configuration. These devices offer low $r_{DS(ON)}$ and ESD protection up to 2kV.

MARKING CODES: CMLDM7003: C30
CMLDM7003G*: C3G
CMLDM7003J: C3J

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage
Drain-Gate Voltage
Gate-Source Voltage
Continuous Drain Current
Maximum Pulsed Drain Current
Power Dissipation (Note 1)
Power Dissipation (Note 2)
Power Dissipation (Note 3)
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V_{DS}	50	V
V_{DG}	50	V
V_{GS}	12	V
I_D	280	mA
I_{DM}	1.5	A
P_D	350	mW
P_D	300	mW
P_D	150	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=5.0\text{V}$			100	nA
I_{GSSF}, I_{GSSR}	$V_{GS}=10\text{V}$			2.0	μA
I_{GSSF}, I_{GSSR}	$V_{GS}=12\text{V}$			2.0	μA
I_{DSS}	$V_{DS}=50\text{V}, V_{GS}=0$			50	nA
BV_{DSS}	$V_{GS}=0, I_D=10\mu\text{A}$	50			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.49		1.0	V
V_{SD}	$V_{GS}=0, I_S=115\text{mA}$			1.4	V
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=50\text{mA}$		1.6	3.0	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=50\text{mA}$		1.3	2.5	Ω
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		1.1	2.0	Ω
g_{FS}	$V_{DS}=10\text{V}, I_D=200\text{mA}$	200			mS
C_{rss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			5.0	pF
C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			50	pF
C_{oss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			25	pF
$Q_g(\text{tot})$	$V_{DS}=25\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.764		nC
Q_{gs}	$V_{DS}=25\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.148		nC
Q_{gd}	$V_{DS}=25\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.156		nC

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²

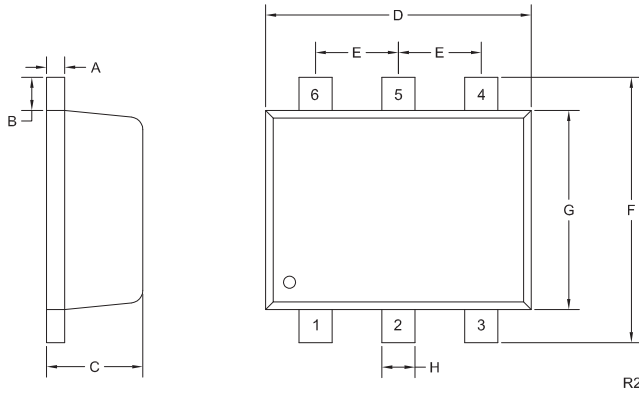
R9 (8-June 2015)

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SOT-563 CASE - MECHANICAL OUTLINE

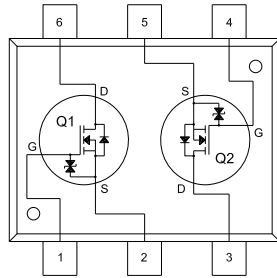


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R2)

PIN CONFIGURATIONS

**CMLDM7003 (USA Pinout)
 CMLDM7003G***



LEAD CODE:

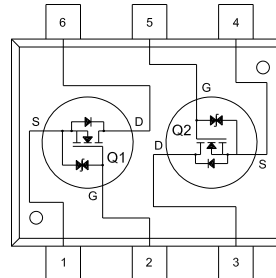
- 1) Gate Q1
- 2) Source Q1
- 3) Drain Q2
- 4) Gate Q2
- 5) Source Q2
- 6) Drain Q1

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CMLDM7003J (Japanese Pinout)



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

MARKING CODE: C3J

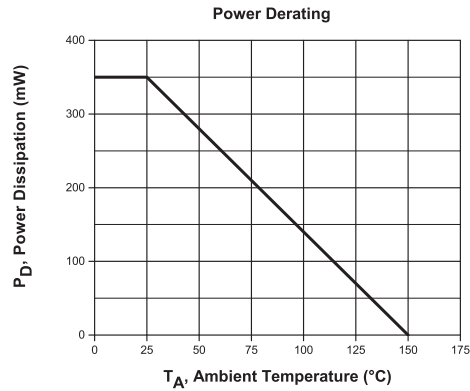
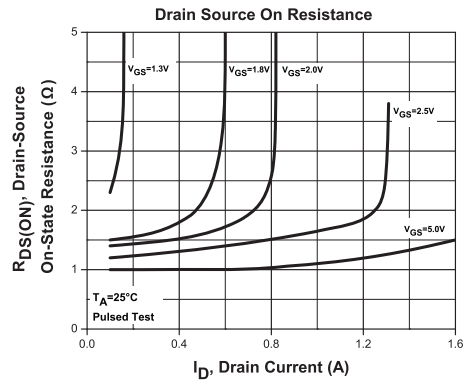
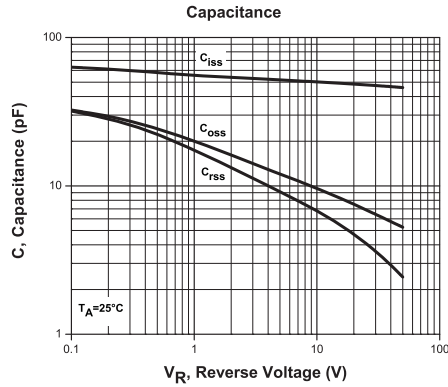
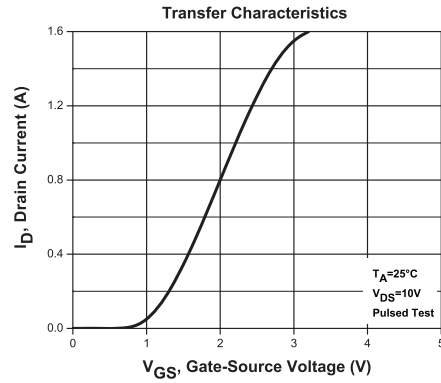
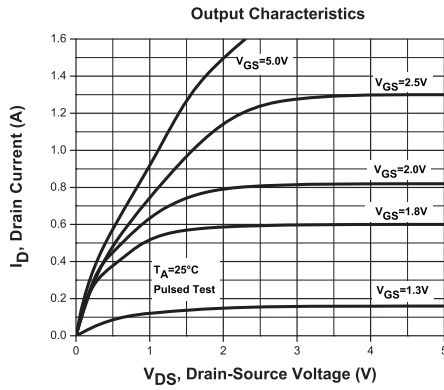
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TYPICAL ELECTRICAL CHARACTERISTICS



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OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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